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L Number	Hits	Search Text	DB	Time stamp
1	3083	(polysilicon and capacitor).clm.	USPAT;	2003/05/13 19:08
		_	US-PGPUB	
2	46	(polysilicon and capacitor and method).ti.	USPAT;	2003/05/13 19:08
_			US-PGPUB	
3	34	(bubbles and capacitor).clm.	USPAT;	2003/05/13 19:08
	010	(US-PGPUB	
4	213	(rough\$4 and capacitor).ab.	USPAT;	2003/05/13 19:09
5	37	/manabad and bubbles a	US-PGPUB	
5	37	(rough\$4 and bubbles).ab.	USPAT;	2003/05/13 19:09
6	13	(rough\$4 and capacitor and etch).ab.	US-PGPUB	0000 /05 /10 00
0	13	(tought and capacitor and etch).ab.	USPAT; US-PGPUB	2003/05/13 19:09
8	41	(rough\$4 and capacitor and etch\$3).ab.	USPAT:	2003/05/13 19:10
	••	(10ught and capacitor and ecches).ab.	US-PGPUB	2003/03/13 19:10
9	437	rough\$4 same capacitor same etch\$3	USPAT;	2003/05/13 19:11
		3 ,	US-PGPUB	2003/03/13 13.11
10	3	(rough\$4 same capacitor same etch\$3) and	USPAT;	2003/05/13 19:12
		bubbles	US-PGPUB	
11	539	(rough\$4 adj surface) same capacitor	USPAT;	2003/05/13 19:13
			US-PGPUB	
-	3079	(polysilicon and capacitor).clm.	USPAT;	2003/05/13 19:07
			US-PGPUB	
-	273	(polysilicon and capacitor and	USPAT;	2003/05/13 19:08
		solution).clm.	US-PGPUB	